鼎德丰
DING DE FENG

NPN Silicon Transistor

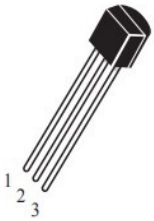
2SC1008

Package:TO-92

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector-base voltage	BV_{CBO}	80	V
Collector-emitter voltage	BV_{CEO}	60	V
Emitter-base voltage	BV_{EBO}	8	V
Collector current	I_{CM}	700	mA
Collector Power Dissipation	P_C	800	mW
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55～+150	℃

TO-92



1. EMITTER
2. BASE
3. COLLECTOR

Electrical Characteristics（Ta=25℃）

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=10μA，I_E=0	80			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=10mA，I_B=0	60			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=10μA，I_C=0	8			V
collector-base cut-off current	I_{CBO}	V_{CB}=80V，I_E=0			0.1	uA
collector-emitter cut-off current	I_{CEO}	V_{CE}=60V，I_B=0			10	uA
emitter-base cut-off current	I_{EBO}	V_{EB}=5V，I_C=0			0.1	uA
DC current gain	H_{FE}	V_{CE}=2V，I_B=50mA	70		400	
		V_{CE}=2V，I_B=5mA	40			
		V_{CE}=2V，I_B=500mA	25			
collector-emitter saturation voltage	V_{CESAT}	I_C=500mA，I_B=50mA			0.4	V
Base-Emitter Saturation Voltage	V_{BESAT}	I_C=500mA，I_B=50mA			1.1	V
Transition frequency	f_T	V_{CE}=10V，I_B=50mA, f=100MHz	30			MH_Z

Classification of H_{FE}

Rank	2SC1008-O	2SC1008-Y	2SC1008-G
Range	70-140	120-240	200-400